Silicon PNP Power Transistors 2SA1227 2SA1227A

DESCRIPTION

- With TO-3PFa package
- Complement to type 2SC2987/2987A
- High power dissipation

APPLICATIONS

- For use in audio frequency power amplifier applications

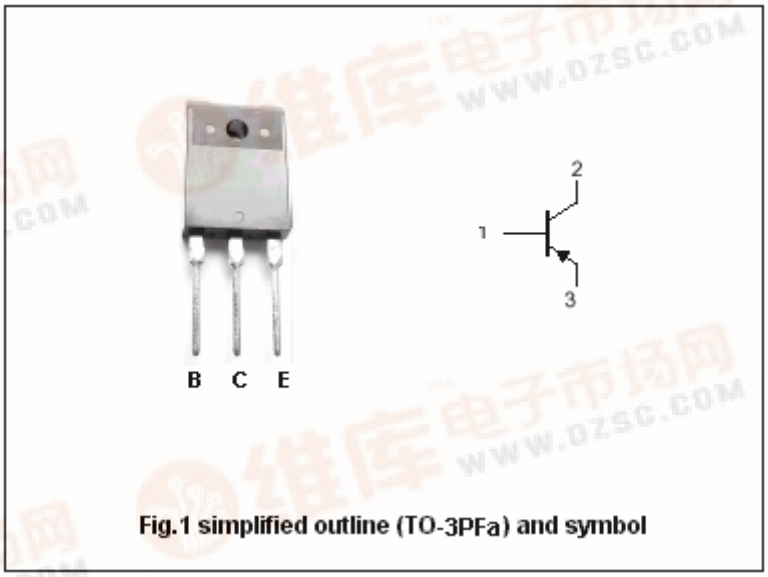

Fig.1 simplified outline (TO-3PFa) and symbol

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2SA1227	Open emitter	-140	V
		2SA1227A		-160	
V_{CEO}	Collector-emitter voltage	2SA1227	Open base	-140	V
		2SA1227A		-160	
V_{EBO}	Emitter-base voltage		Open collector	-5	V
I_C	Collector current			-12	A
I_{CM}	Collector current-peak			-20	A
P_T	Total power dissipation		T_C=25℃	120	W
T_j	Junction temperature			150	℃
T_{stg}	Storage temperature			-55~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V_{CEsat}	Collector-emitter saturation voltage	I_C=-5A ;I_B=-0.5A		-0.8	-1.5	V
V_{BEsat}	Base-emitter saturation voltage	I_C=-5A ;I_B=-0.5A		-1.5	-2.0	V
I_{CBO}	Collector cut-off current	V_{CB}=-140V; I_E=0			-50	μA
I_{EBO}	Emitter cut-off current	V_{EB}=-3V; I_C=0			-50	μA
h_{FE-1}	DC current gain	I_C=-2A ; V_{CE}=-5V	60		320	
h_{FE-2}	DC current gain	I_C=-5A ; V_{CE}=-5V	40			
C_{OB}	Output capacitance	I_E=0 ; V_{CB}=-10V;f=1MHz		280		pF
f_T	Transition frequency	I_C=-1A ; V_{CE}=-5V		60		MHz

◆ **h_{FE-1} classifications**

R	Q	P
60-120	100-200	160-320

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PACKAGE OUTLINE

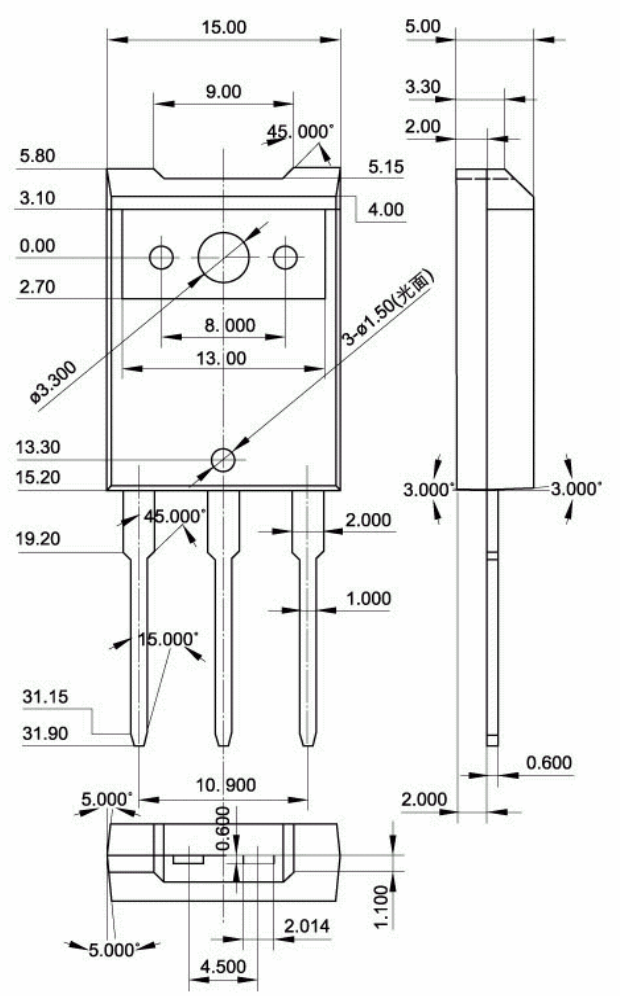

Fig.2 Outline dimensions (unindicated tolerance:±0.30mm)